

# ABSTRACT OF THE DISCLOSURE

A resistance-reduced semiconductor device and  
fabrication thereof. The semiconductor device of the  
invention includes a semiconductor device body exposing  
at least one silicon-containing portion, a metal silicide  
layer with a first resistivity overlying the silicon-  
containing portion and a conductor layer with a second  
resistivity overlying the metal silicide layer, wherein  
the second resistivity is smaller than the first  
resistivity.